
2SC1344, 2SC1345

Silicon NPN Epitaxial

HITACHI

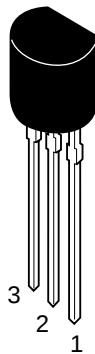
ADE-208-1052A (Z)
2nd. Edition
Mar. 2001

Application

Low frequency low noise amplifier

Outline

TO-92 (1)



- 1. Emitter
- 2. Collector
- 3. Base

2SC1344, 2SC1345

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	2SC1344	2SC1345	Unit
Collector to base voltage	V_{CBO}	30	55	V
Collector to emitter voltage	V_{CEO}	30	50	V
Emitter to base voltage	V_{EBO}	5	5	V
Collector current	I_C	100	100	mA
Collector power dissipation	P_C	200	200	mW
Junction temperature	T_j	150	150	°C
Storage temperature	T_{stg}	−55 to +150	−55 to +150	°C

Electrical Characteristics (Ta = 25°C)

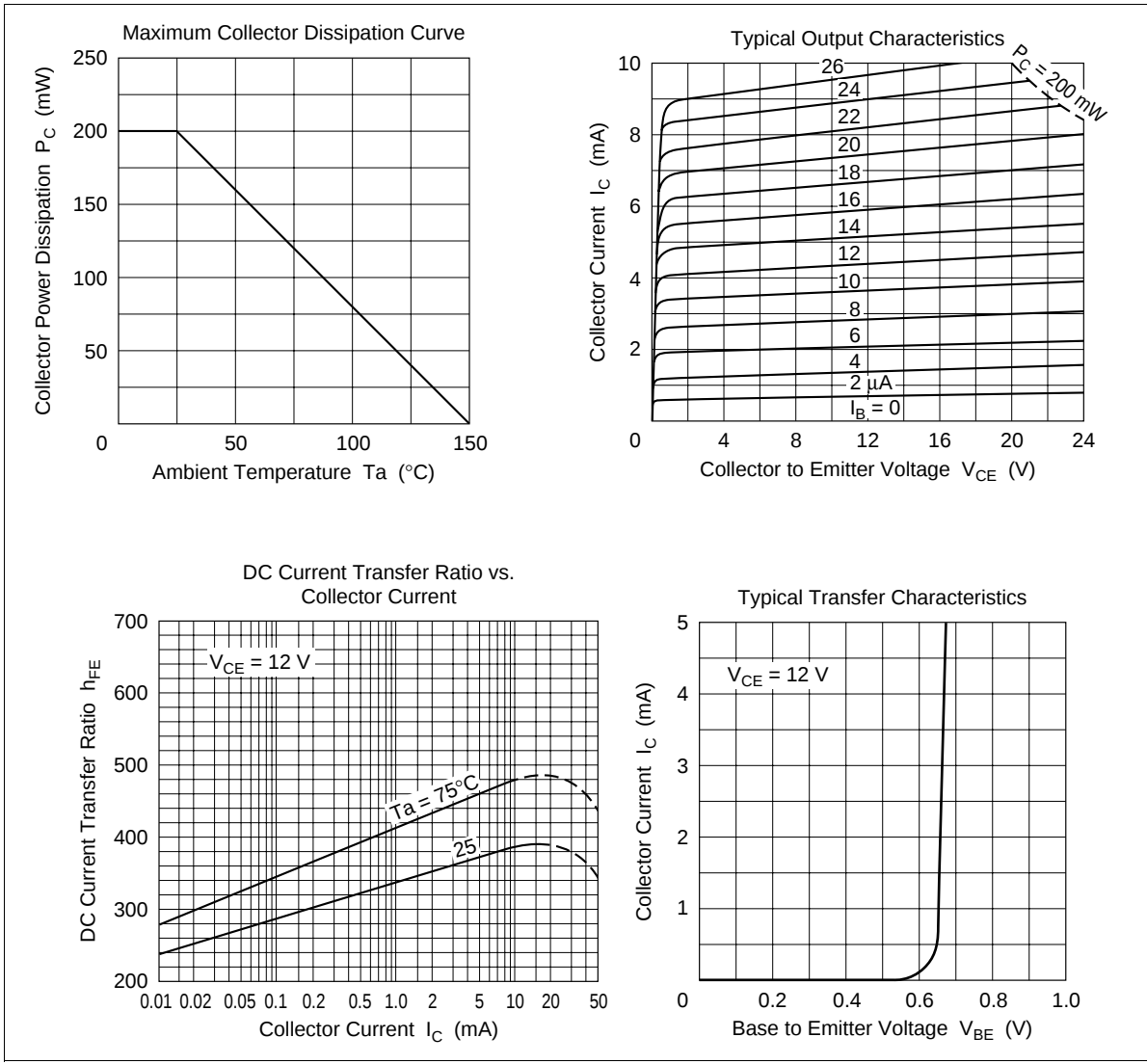
Item	Symbol	2SC1344			2SC1345			Unit	Test conditions
		Min	Typ	Max	Min	Typ	Max		
Collector to base breakdown voltage	$V_{(BR)CBO}$	30	—	—	55	—	—	V	$I_C = -10\ \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	30	—	—	50	—	—	V	$I_C = 1\ mA, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	—	—	5	—	—	V	$I_E = 10\ \mu A, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	0.5	—	—	0.5	μA	$V_{CB} = 18\ V, I_E = 0$
Emitter cutoff current	I_{EBO}	—	—	0.5	—	—	0.5	μA	$V_{EB} = 2\ V, I_C = 0$
DC current transfer ratio	h_{FE}^{*1}	250	—	1200	250	—	1200		$V_{CE} = 12\ V, I_C = 2\ mA$
Base to emitter voltage	V_{BE}	—	—	0.75	—	—	0.75	V	$V_{CE} = 12\ V, I_C = 2\ mA$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	0.5	—	—	0.5	V	$I_C = 10\ mA, I_B = 1\ mA$
Gain bandwidth product	f_T	—	230	—	—	230	—	MHz	$V_{CE} = 12\ V, I_C = 2\ mA$
Collector output capacitance	C_{ob}	—	—	3.5	—	—	3.5	pF	$V_{CB} = 10\ V, I_E = 0, f = 1\ MHz$
Noise figure	NF	—	—	8	—	—	8	dB	$V_{CE} = 6\ V, I_C = 0.1\ mA, f = 10\ Hz, R_g = 10\ k\Omega$
		—	—	1	—	—	1	dB	$V_{CE} = 6\ V, I_C = 0.1\ mA, f = 1\ kHz, R_g = 10\ k\Omega$

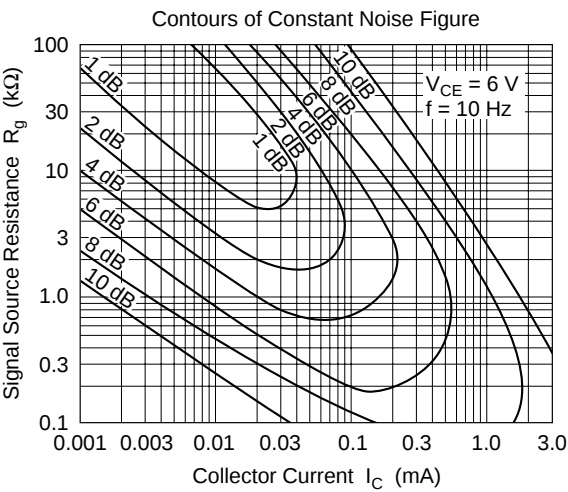
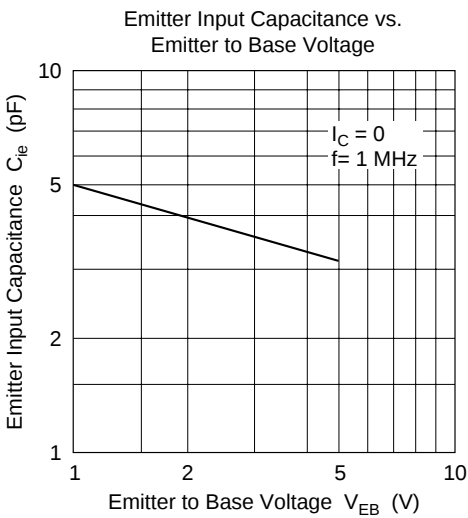
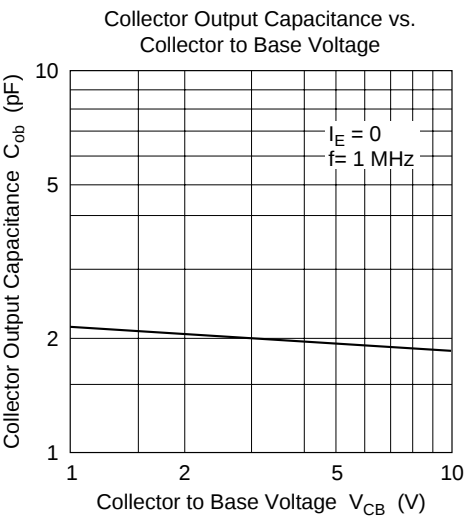
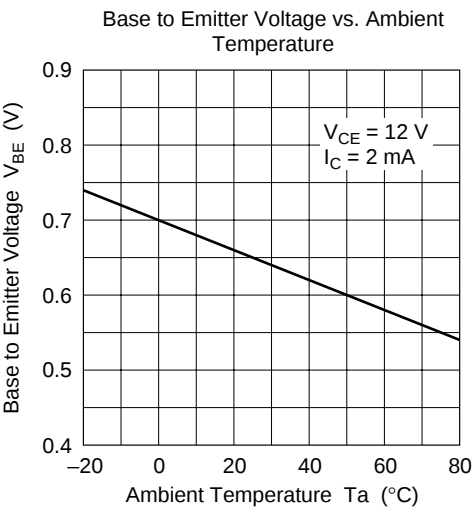
Note: 1. The 2SC1344 and 2SC1345 are grouped by h_{FE} as follows.

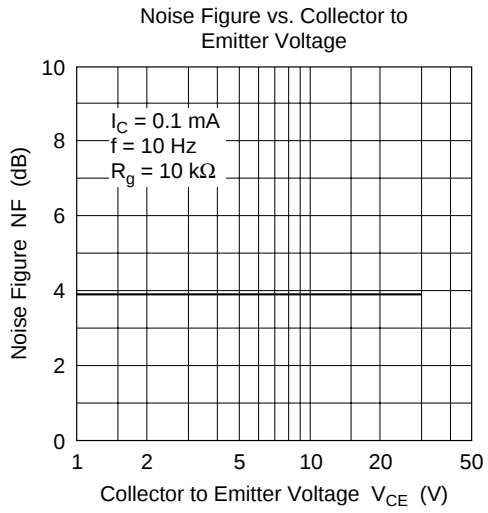
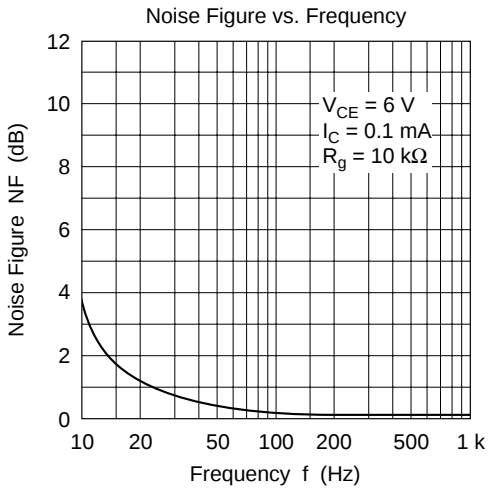
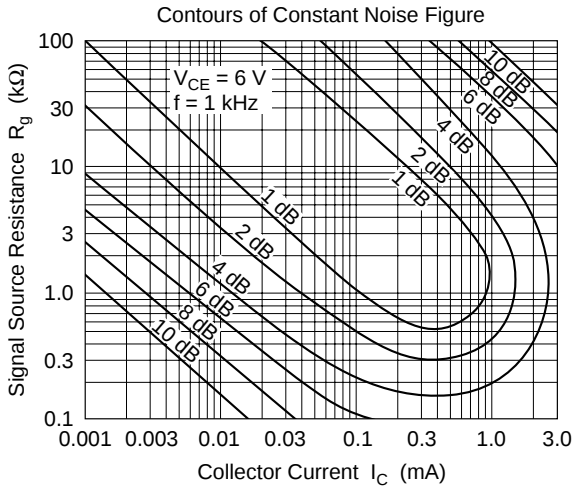
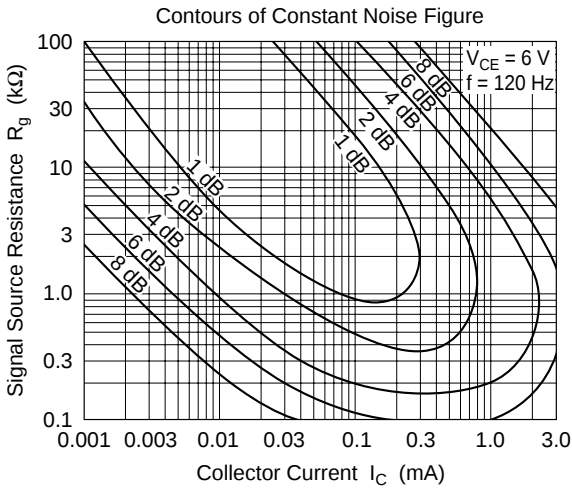
D	E	F
250 to 500	400 to 800	600 to 1200

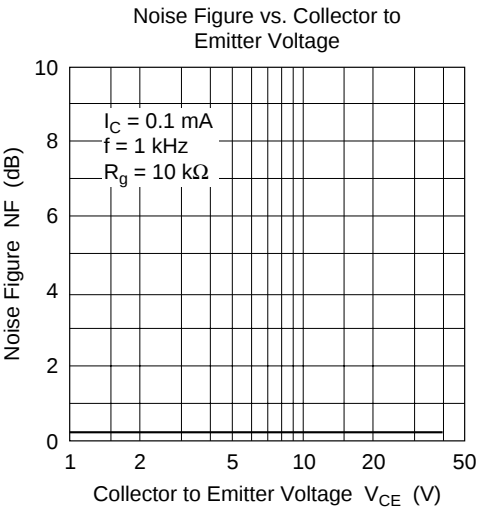
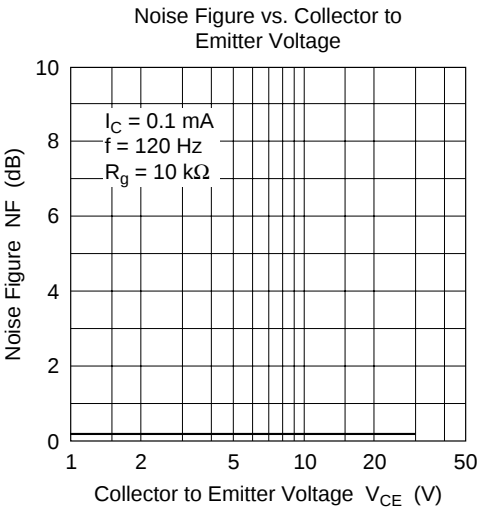
Small Signal h Parameters ($V_{CE} = 5V$, $I_C = 0.1 \text{ mA}$, $f = 270 \text{ Hz}$, $T_a = 25^\circ\text{C}$, Emitter common)

Item	Symbol	D	E	F	Unit
Input impedance	hie	110	170	240	kΩ
Voltage feedback ratio	hre	9.5	14.5	16	$\times 10^{-4}$
Current transfer ratio	hfe	340	540	825	
Output admittance	hoe	12.0	12.5	13.5	μS



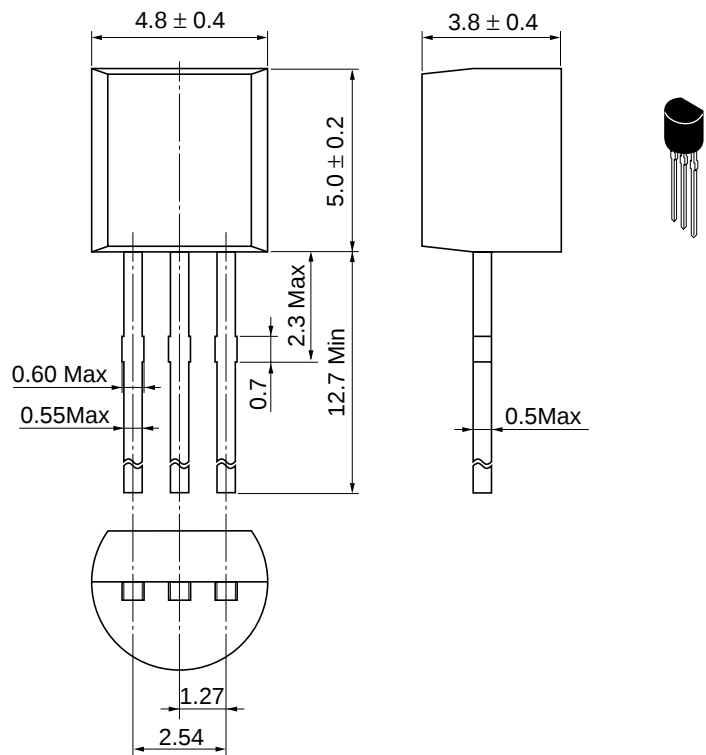






Package Dimensions

As of January, 2001
Unit: mm



Hitachi Code	TO-92 (1)
JEDEC	Conforms
EIAJ	Conforms
Mass (reference value)	0.25 g

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HITACHI

Hitachi, Ltd.

Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL	NorthAmerica	:	http://semiconductor.hitachi.com/
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For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose, CA 95134
Tel: <1> (408) 433-1990
Fax: <1> (408) 433-0223

Hitachi Europe GmbH
Electronic Components Group
Dornacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 585160

Hitachi Asia Ltd.
Hitachi Tower
16 Collyer Quay #20-00,
Singapore 049318
Tel: <65>-538-6533/538-8577
Fax: <65>-538-6933/538-3877
URL: <http://www.hitachi.com.sg>

Hitachi Asia Ltd.
(Taipei Branch Office)
4/F, No. 167, Tun Hwa North Road,
Hung-Kuo Building,
Taipei (105), Taiwan
Tel: <886>-(2)-2718-3666
Fax: <886>-(2)-2718-8180
Telex: 23222 HAS-TP
URL: <http://www.hitachi.com.tw>

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower,
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon,
Hong Kong
Tel: <852>-(2)-735-9218
Fax: <852>-(2)-730-0281
URL: <http://www.hitachi.com.hk>

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